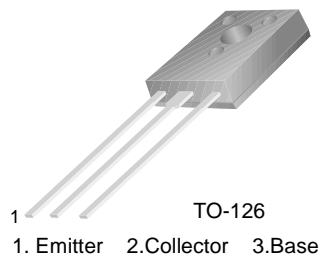


## MJE350

### High Voltage General Purpose Applications

- High Collector-Emitter Breakdown Voltage
- Suitable for Transformer
- Complement to MJE340



### ..PNP Epitaxial Silicon Transistor

#### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	- 300	V
$V_{CEO}$	Collector-Emitter Voltage	- 300	V
$V_{EBO}$	Emitter-Base Voltage	- 5	V
$I_C$	Collector Current	- 500	mA
$P_C$	Collector Dissipation ( $T_C=25^\circ\text{C}$ )	20	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

#### Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C = - 1\text{mA}, I_B = 0$	-300		V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = - 300\text{V}, I_E = 0$		-100	$\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current	$V_{BE} = - 3\text{V}, I_C = 0$		-100	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$V_{CE} = - 10\text{V}, I_C = - 50\text{mA}$	30	240	

# Typical Characteristics

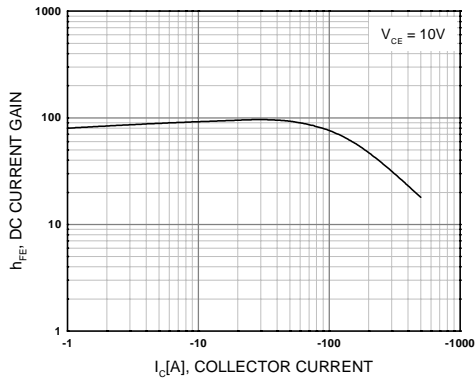


Figure 1. DC current Gain

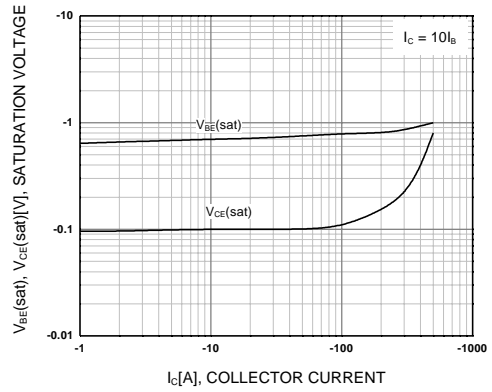


Figure 2. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

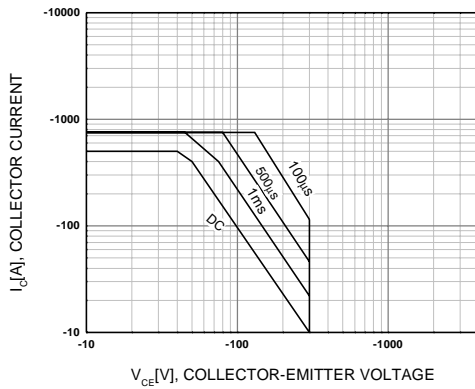


Figure 3. Safe Operating Area

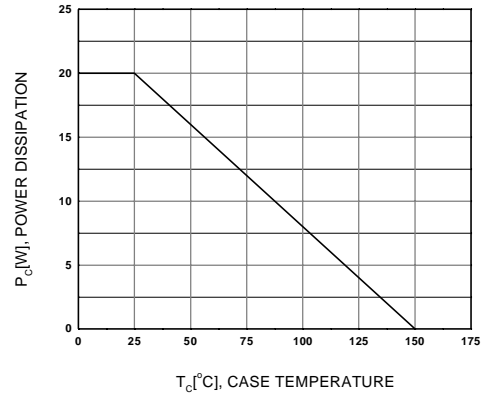
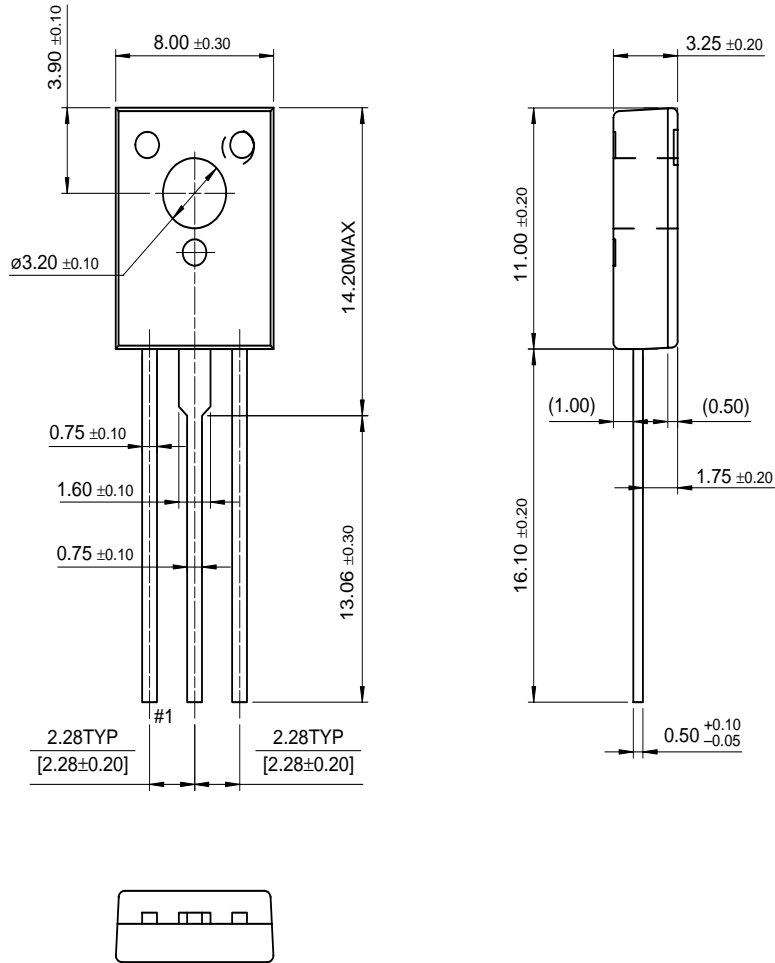


Figure 4. Power Derating

# Package Dimensions

## TO-126



Dimensions in Millimeters